Low-power dual 2-input AND gate Rev. 7 — 18 January 2013

Product data sheet

General description 1.

The 74AUP2G08 provides the dual 2-input AND function.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1 000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C



Low-power dual 2-input AND gate

3. Ordering information

Table 1. Ordering	g information			
Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G08DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP2G08GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1
74AUP2G08GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089
74AUP2G08GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3 \times 2 \times 0.5$ mm	SOT996-2
74AUP2G08GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-2
74AUP2G08GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116
74AUP2G08GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

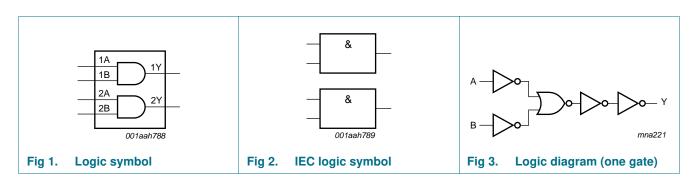
4. Marking

Table 2.Marking codes

3	
Type number	Marking code ^[1]
74AUP2G08DC	p08
74AUP2G08GT	p08
74AUP2G08GF	pE
74AUP2G08GD	p08
74AUP2G08GM	p08
74AUP2G08GN	pE
74AUP2G08GS	pE

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

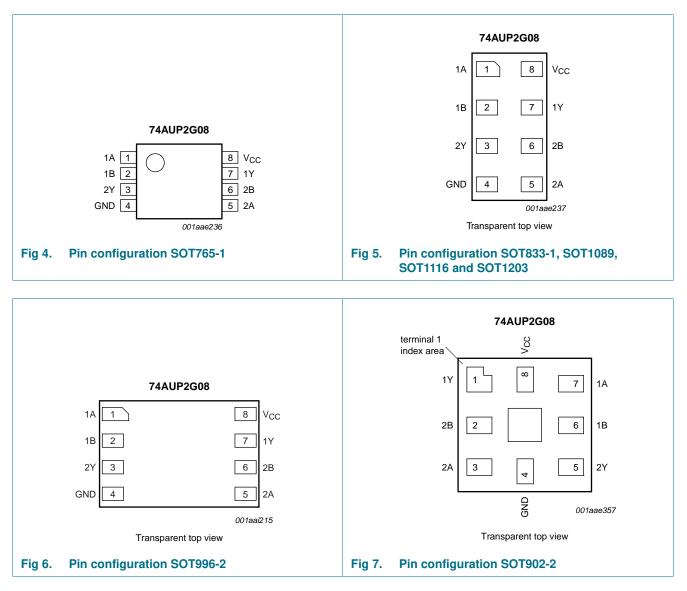
5. Functional diagram



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Pinning information 6.

6.1 Pinning



6.2 Pin description

Symbol	Pin	Pin		
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2		
1A, 2A	1, 5	7, 3	data input	
1B, 2B	2, 6	6, 2	data input	
GND	4	4	ground (0 V)	
1Y, 2Y	7, 3	1, 5	data output	
V _{CC}	8	8	supply voltage	
74AUP2G08	All information provided in t	his document is subject to legal discl	aimers. © NXP B.V. 2013. All rigi	hts reserved.
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7. Functional description

Table 4.Function table^[1]

Input		Output
nA	nB	nY
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

[1] H = HIGH voltage level;

L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V ₁ < 0 V	-50	-	mA
VI	input voltage		<u>1</u> –0.5	+4.6	V
Ι _{ΟΚ}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>1</u> –0.5	+4.6	V
I _O	output current	$V_{O} = 0 V \text{ to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly at 8.0 mW/K. For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	-	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	25 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_O = –20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.1	μA
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μA
∆I _{OFF}	additional power-off leakage current	V_1 or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μA
lcc	supply current	$\label{eq:VI} \begin{array}{l} V_I = GND \text{ or } V_{CC}; \ I_O = 0 \ A; \\ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	0.5	μA
Δl _{CC}	additional supply current		<u>[1]</u> -	-	40	μA
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.6	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.3	-	pF

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	Parameter	; voltages are referenced to GND (groun Conditions	Min	Tup	Max	Unit
-		Conditions	IVIITI	Тур	Max	Unit
	40 °C to +85 °C	V 0.8.V	0.70)/			V
VIH	HIGH-level input voltage	$\frac{V_{CC} = 0.8 \text{ V}}{V_{CC} = 0.8 \text{ V}}$	0.70 × V _{CC}		-	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{ОН}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = –20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3\times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
l	input leakage current	$V_{I} = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μA
I _{OFF}	power-off leakage current	$V_{\rm I}$ or $V_{\rm O} = 0$ V to 3.6 V; $V_{\rm CC} = 0$ V	-	-	±0.5	μΑ
Δl _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μ Α
сс	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
Δl _{CC}	additional supply current		[1] -	-	50	μA

Table 7. Static characteristics ... continued

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.75 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25 \times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V} \text{ to } 1.95 \text{ V}$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	$V_{CC}-0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μA
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.75	μA
∆I _{OFF}	additional power-off leakage current		-	-	±0.75	μA
CC	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	1.4	μA
∆I _{CC}	additional supply current		[1] -	-	75	μA

Static characteristics ... continued Table 7.

[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Dynamic characteristics Table 8.

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		Ta	_{mb} = 25 °	C	T _{amb} =	-40 °C to	o +125 ℃	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 p	ρF									
pd	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	17.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V		2.6	5.1	10.8	2.1	11.7	12.9	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		1.6	3.7	6.5	1.5	7.5	8.3	ns
		V _{CC} = 1.65 V to 1.95 V		1.3	3.0	5.2	1.3	6.1	6.7	ns
		V_{CC} = 2.3 V to 2.7 V		1.1	2.4	4.0	1.0	4.8	5.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.0	2.2	3.5	0.9	4.3	4.8	ns
C _L = 10	pF									
pd	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	20.6	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V		2.4	6.0	12.5	2.2	13.6	15.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.0	4.3	7.6	1.8	8.9	9.8	ns
		V _{CC} = 1.65 V to 1.95 V		1.7	3.6	6.1	1.6	7.2	7.9	ns
		V_{CC} = 2.3 V to 2.7 V		1.4	2.9	4.8	1.3	5.7	6.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.3	2.7	4.2	1.2	4.7	5.2	ns
C _L = 15	pF									
pd	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	24.1	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V		3.4	6.8	14.2	3.1	15.7	17.3	ns
		V _{CC} = 1.4 V to 1.6 V		2.3	4.9	8.6	2.1	10.1	11.2	ns
		V _{CC} = 1.65 V to 1.95 V		1.9	4.0	6.9	1.8	8.2	9.0	ns
		V_{CC} = 2.3 V to 2.7 V		1.7	3.4	5.5	1.6	6.5	7.2	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.5	3.1	4.8	1.5	5.9	6.5	ns
C _L = 30	pF									
od	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	34.4	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V		4.6	9.1	19.4	4.1	21.8	24.0	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V		3.4	6.4	11.5	2.9	13.6	15.0	ns
		V _{CC} = 1.65 V to 1.95 V		2.6	5.3	9.1	2.4	10.9	12.1	ns
		V_{CC} = 2.3 V to 2.7 V		2.3	4.5	7.2	2.2	8.6	9.5	ns
		V _{CC} = 3.0 V to 3.6 V		2.2	4.2	6.2	2.1	7.5	8.3	ns

Low-power dual 2-input AND gate

Symbol	Parameter	Conditions	Ta	T _{amb} = 25 °C			= -40 °C to) +125 °C	Unit
				Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 p	F, 10 pF, 15 pF and	30 pF							
C _{PD} power dissipation	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}}$	L						
	capacitance	$V_{CC} = 0.8 V$	-	2.5	-	-	-	-	pF
		V _{CC} = 1.1 V to 1.3 V	-	2.6	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	2.7	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	2.8	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	3.2	-	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	3.7	-	-	-	-	pF

Dynamic characteristics ... continued Table 8.

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

12. Waveforms

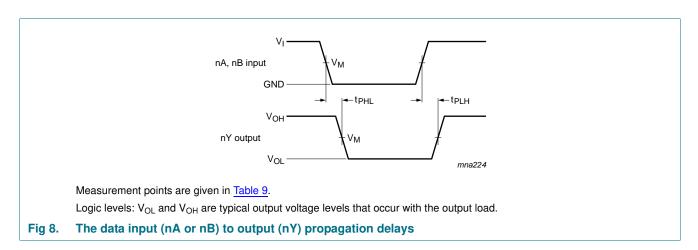


Table 9. **Measurement points**

Supply voltage	Output	Input		
V _{cc}	V _M	V _M	V _I	t _r = t _f
0.8 V to 3.6 V	$0.5 imes V_{CC}$	$0.5\times V_{CC}$	V _{CC}	\leq 3.0 ns

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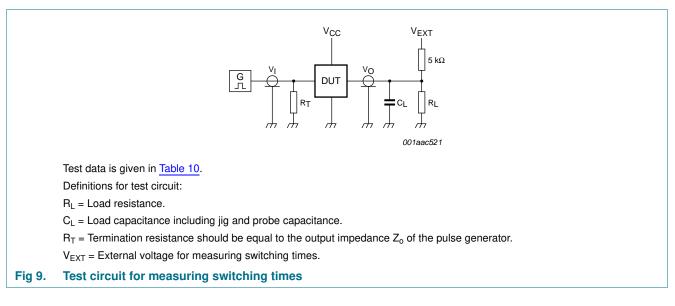


Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{cc}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times, $R_L = 5 k\Omega$.

For measuring propagation delays, set-up and hold times and pulse width, R_L = 1 M Ω .

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13. Package outline

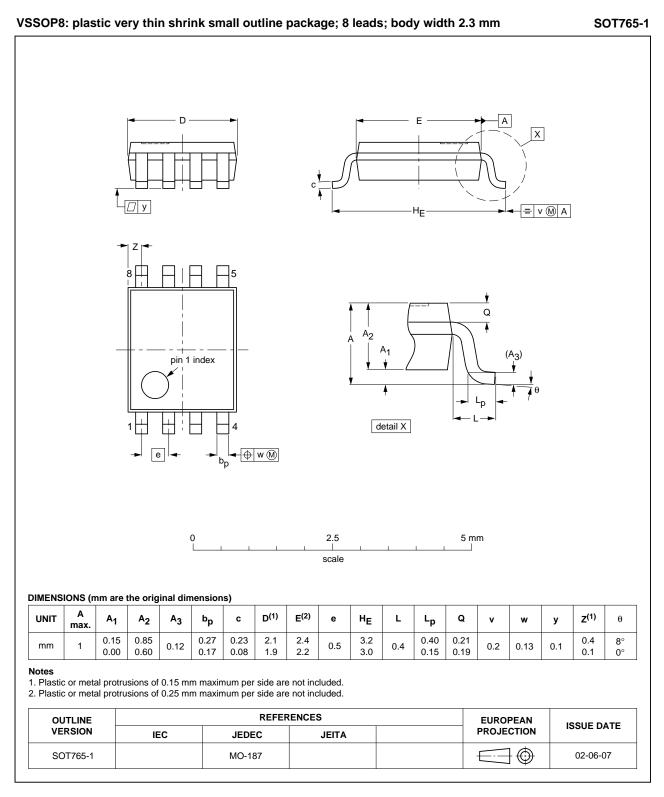


Fig 10. Package outline SOT765-1 (VSSOP8)

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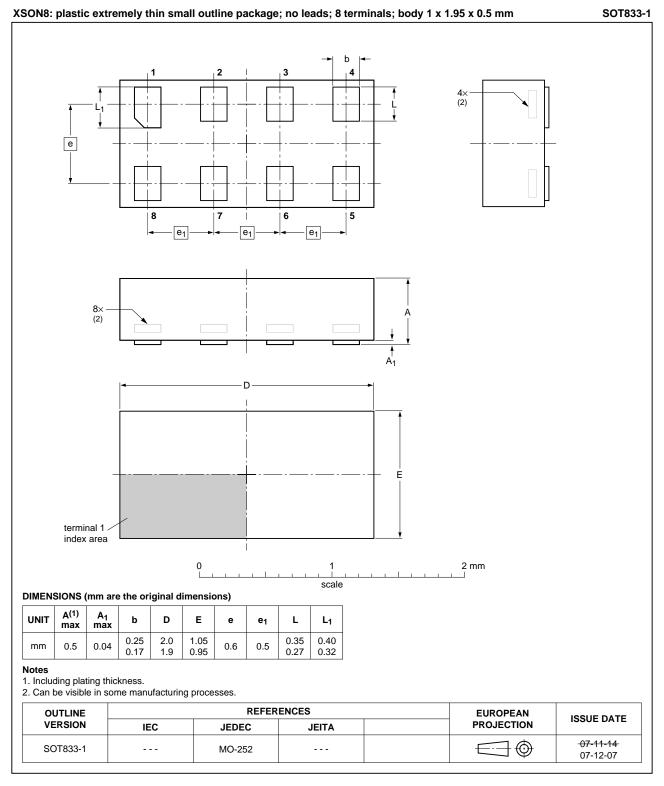
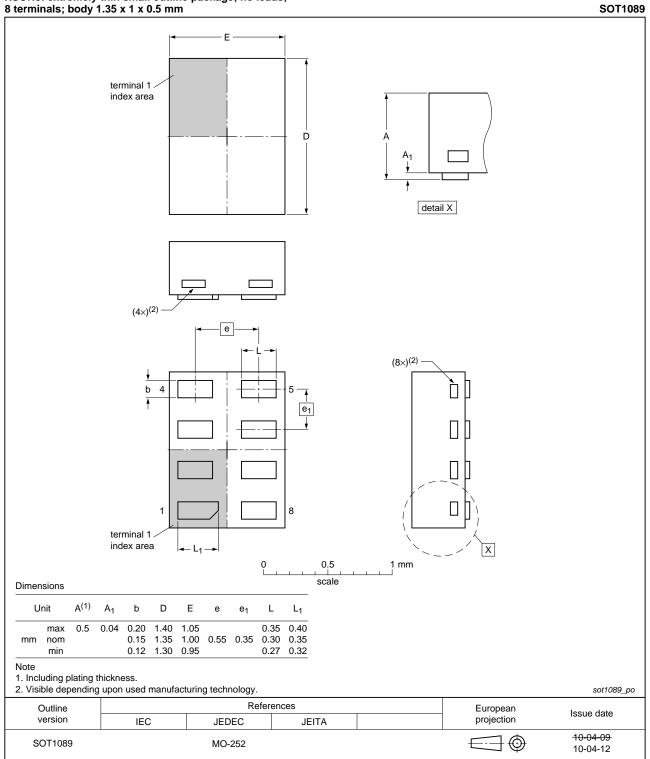


Fig 11. Package outline SOT833-1 (XSON8)

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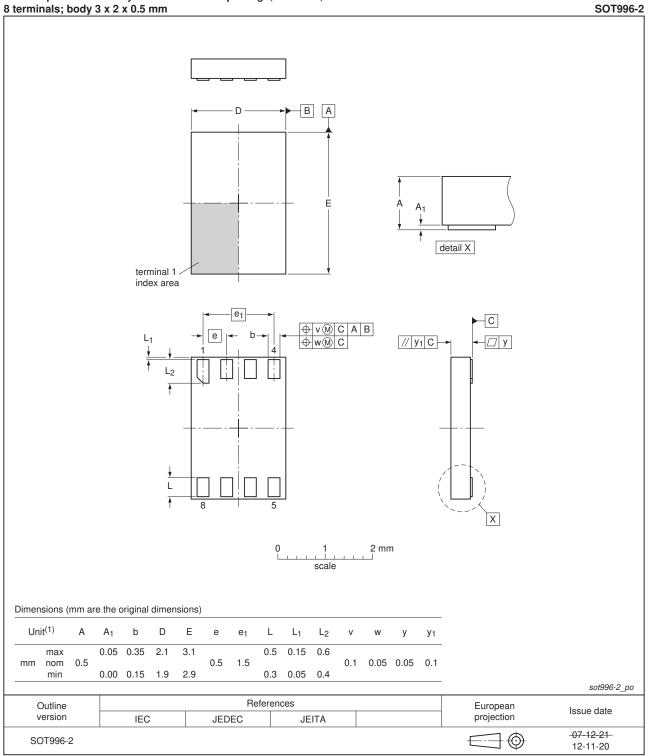


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 12. Package outline SOT1089 (XSON8)

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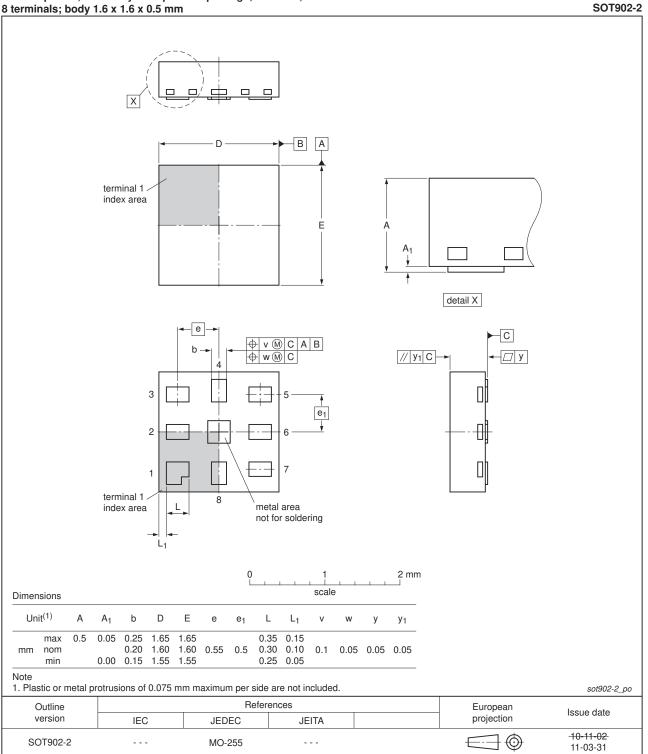


XSON8: plastic extremely thin small outline package; no leads;

Fig 13. Package outline SOT996-2 (XSON8)

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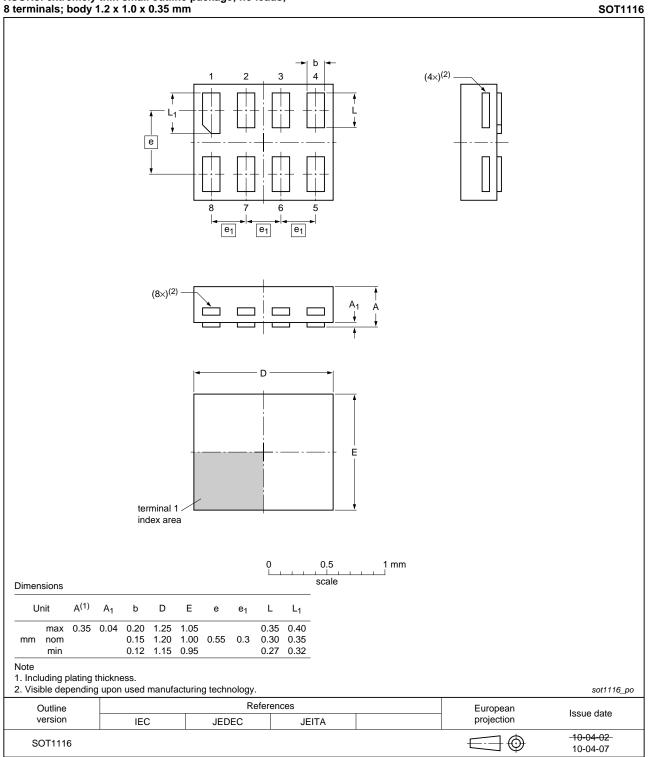


XQFN8: plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm

Fig 14. Package outline SOT902-2 (XQFN8)

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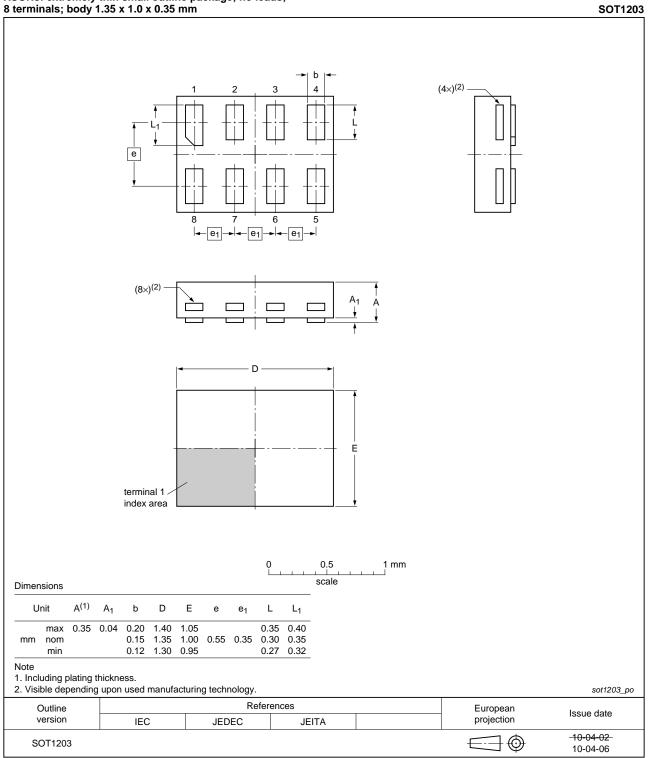


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 15. Package outline SOT1116 (XSON8)

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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1203 (XSON8)

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14. Abbreviations

Table 11. Abbreviations		
Description		
Charged Device Model		
Device Under Test		
ElectroStatic Discharge		
Human Body Model		
Machine Model		
k	Description Charged Device Model Device Under Test ElectroStatic Discharge Human Body Model	

15. Revision history

Document ID Release 74AUP2G08 v.7 20130118 Modifications: • For ty 74AUP2G08 v.6 20120607 74AUP2G08 v.5 20111201	Table 12. Revision history						
Modifications: • For ty 74AUP2G08 v.6 20120607	date Data sheet status	Change notice	Supersedes				
74AUP2G08 v.6 20120607	Product data sheet	-	74AUP2G08 v.6				
	pe number 74AUP2G08GD XSON	8U has changed to XSON8.					
74ALIP2G08 v 5 20111201	Product data sheet	-	74AUP2G08 v.5				
	Product data sheet	-	74AUP2G08 v.4				
74AUP2G08 v.4 20101109	Product data sheet	-	74AUP2G08 v.3				
74AUP2G08 v.3 20080529	Product data sheet	-	74AUP2G08 v.2				
74AUP2G08 v.2 20080407	Product data sheet	-	74AUP2G08 v.1				
74AUP2G08 v.1 20061006	Product data sheet	-	-				

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16. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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